

# 8th "Trento" Workshop on Advanced Silicon Radiation Detectors (3D and p-type)

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## Modelling of 3D detectors and comparison with data

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Modelling of charge collection in 3D silicon detectors is described. The modelling is extended to irradiated devices using the deep acceptor model and combined with avalanche multiplication. Modelling of charge transport in the electrodes for full-3D devices is described. The results are compared to data from test beams and also x-ray scans at the Diamond synchrotron at the Rutherford Appleton Laboratory. Conclusions are made on defect modelling at high fluences, avalanche effects, and charge transport in electrodes.

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